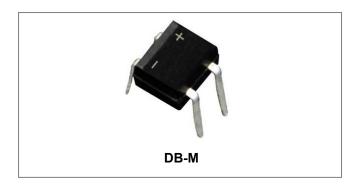






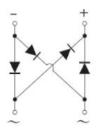
# DF151 THRU DF157 SINGLE-PHASE GLASS PASSIVATED SILICON BRIDGE RECTIFIER



#### **Features**

- · Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Plastic material-UL flammability 94V-0
- Terminals finish: 100% Pure Tin
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

#### **Circuit Diagram**



#### **Mechanical Data**

- Case: DB-M, Molded plastic
- Terminals: Plated leads solderable per MIL-STD-202,
  - Method 208
- Polarity: as marked on case
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version

#### Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase half wave 60Hz, resistive or inductive load. For capacitive load current derate by 20%.

Characteristic	Symbol	DF151	DF152	DF153	DF154	DF155	DF156	DF157	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	V
Average Forward Output Current (Note 1) @ T <sub>A</sub> =40°C	I <sub>F(AV)</sub>	1.5						Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	55						А	







## **Electrical Characteristics:**

Characteristic	Symbol	DF151	DF152	DF153	DF154	DF155	DF156	DF157	Units
Maximum Forward Voltage Drop per Bridge Element @I <sub>F</sub> =1.5A, T <sub>J</sub> =25°C	V <sub>F</sub>	1.1					V		
Peak Reverse Current @T <sub>A</sub> = 25°C At Rated DC Blocking Voltage @T <sub>A</sub> = 125°C	I <sub>R</sub>	5 500					μA		
Typical Junction Capacitance (Note 2)	Сл				25				pF

<sup>\*</sup> Pulse width < 300 μs, duty cycle < 2%

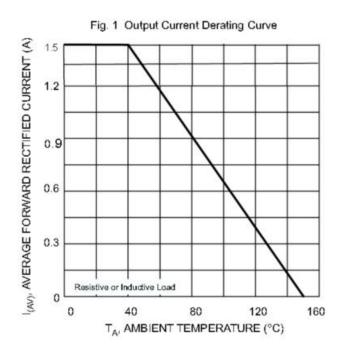
### **Thermal-Mechanical Specifications:**

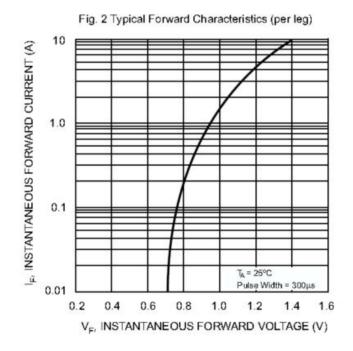
Characteristic	Symbol	DF151	DF152	DF153	DF154	DF155	DF156	DF157	Units
Typical Thermal Resistance Junction to Ambient	R <sub>0JA</sub>	JA 40						°C/W	
Typical Thermal Resistance Junction to Lead	Rejl						°C/W		
Operating Junction and Storage Temperature Range	T <sub>J</sub> ,T <sub>STG</sub>	-55 to + 150					°C		

Note: 1. Mounted on glass epoxy PC board with 1.3mm<sup>2</sup> solder pad.

2. Measured at 1.0 MHZ and applied reverse voltage of 4.0 VDC

## **Ratings and Characteristics Curves**





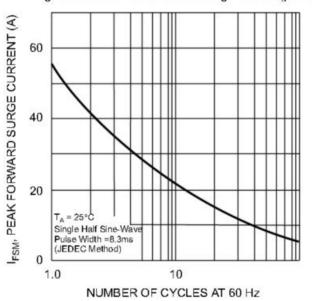
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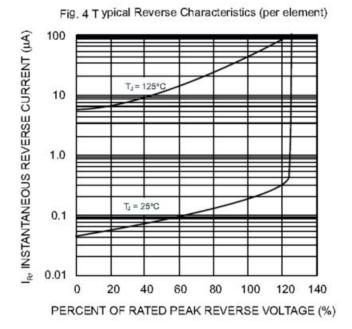




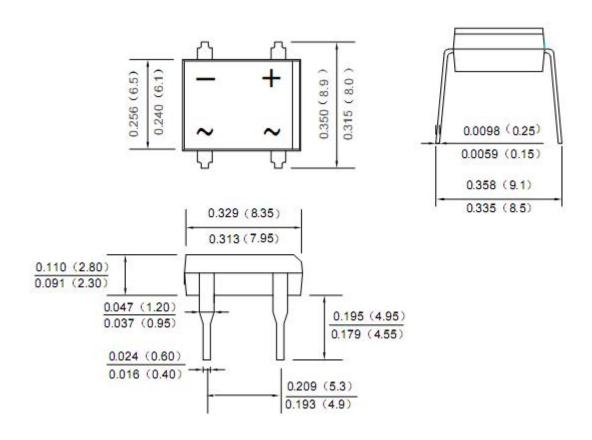


Fig. 3 Maximum Peak Forward Surge Current (per leg)





## **Mechanical Dimensions DB-M(Inches/Millimeters)**



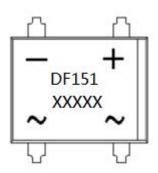
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  - http://www.smc-diodes.com sales@ smc-diodes.com •







## **Marking Diagram**



Where XXXXX is YYWWL

DF151 = Type Number
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin

Epoxy resin UL:94V-0

## **Ordering Information**

Device	Package	Plating	Shipping		
DF151 THRU DF157	DB-M(Pb-Free)	Pure Sn	50pcs / tube		

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

#### **DF151 THRU DF157**



#### Technical Data Data Sheet N1736, Rev. B





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